


APPLICATION DATA SHEET

Electronic Version v14

Stylesheet Version v14.0

Title of Invention	METHOD OF FORMING ADJACENT HOLES ON A SEMICONDUCTOR SUBSTRATE	
Application Type : regular, utility Attorney Docket Number : NTCP0011USA		
Correspondence address: Customer Number: 027765		
		
Inventors Information: <u>Inventor 1:</u> Applicant Authority Type: Inventor Citizenship: TW Given Name: Tse-Yao Family Name: Huang Residence: City of Residence: Taipei City Country of Residence: TW Address-1 of Mailing Address: 13F-1, No. 142, Sec. 2, Nan-Kang Rd. Address-2 of Mailing Address: City of Mailing Address: Taipei City State of Mailing Address: Postal Code of Mailing Address: Country of Mailing Address: TW Phone: Fax: E-mail: <u>Inventor 2:</u> Applicant Authority Type: Inventor Citizenship: TW Given Name: Yi-Nan Family Name: Chen Residence: City of Residence: Taipei City		

Country of Residence: TW
Address-1 of Mailing Address: No. 4, Lane 151, Chien-Min Rd., Pei-Tou
Address-2 of Mailing Address:
City of Mailing Address: Taipei City
State of Mailing Address:
Postal Code of Mailing Address:
Country of Mailing Address: TW
Phone:
Fax:
E-mail:

Attorney Information:

practitioner(s) at Customer Number:

027765



as our attorney(s) or agent(s) to prosecute the application identified above, and to transact all business in the United States Patent and Trademark Office connected therewith.